

2SK23A

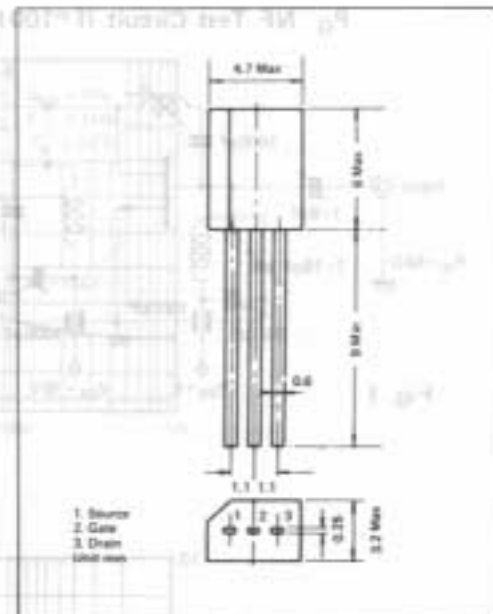
2SK23A

Silicon N-Channel Junction FET

- 汎用DC-to-VHF Use, Low Noise, High Reliability
- Economical Type: 2SK107
- Dual Type: 2SK58

絶対最大定格 Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Characteristics	Symbol	2SK23A-8	2SK23A-9
Drain-to-Gate Voltage	V_{DGO}	27V	40V
Source-to-Gate Voltage	V_{SGO}	9V	
Drain Current	I_D	20 mA	
Gate Current	I_G	10 mA	
Power Dissipation	P	250 mW	
Junction Temperature	T_j	100°C	
Storage Temperature	T_{stg}	-30--+120°C	



電気的特性 Electrical Characteristics $T_a = 25^\circ\text{C}$

Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit
Source-to-Gate Voltage	V_{SGO}	$I_{SG} = 10\mu\text{A}$	9			V
Gate Cutoff Current	I_{GSS}	$V_{GS} = -6\text{V}, V_{DS} = 0$		-0.05	-10	nA
Drain Saturation Current	I_{DSS}	$V_{DS} = 10\text{V}, V_{GS} = 0$	2.7		12.1	mA
Pinch-off Voltage	V_p	$V_{DS} = 10\text{V}, I_D = 30\mu\text{A}$	-0.45		-3.85	V
Forward Transfer Conductance	g_m	$V_{DS} = 10\text{V}, V_{GS} = 0,$ $f = 1\text{ kHz}$	2.7			$\text{m}\Omega$
Input Impedance Y11S	r_p	$V_{DS} = 10\text{V}, V_{GS} = 0,$		8		$\text{k}\Omega$
	C_p	$f = 100\text{ MHz}$		5		pF
Output Impedance Y22S	r_p	$V_{DS} = 10\text{V}, V_{GS} = 0,$		20		$\text{k}\Omega$
	C_p	$f = 100\text{ MHz}$		2		pF
Reverse Transfer Capacitance	C_{dg}	$V_{DS} = 10\text{V}, f = 1\text{ MHz}$		1.8		pF
Input Noise Voltage	e	$V_{DS} = 10\text{V}, V_{GS} = 0,$		13		$\text{nV}/\text{Hz}^{1/2}$
Noise Figure	NF	$R_g = 10\text{ k}\Omega, f = 1\text{ kHz}$		0.1		dB
Power Gain	P_G	$V_{DS} = 10\text{V}, V_{GS} = 0,$		18		dB
Noise Figure	NF	$f = 100\text{ MHz}, \text{Fig. 1}$		2		dB

規格細分 Classifications

Rank	$I_{DSS} (V_{DS} = 10\text{V}, V_{GS} = 0)$	$-V_p (V_{DS} = 10\text{V}, I_D = 30\mu\text{A})$
2SK23A-8-9	2	2.7- 5.5
	3	4.5- 7.7
	4	6.3- 9.9
	5	8.1-12.1